TOSHIBA Photocoupler GaAlAs Ired & Photo-IC

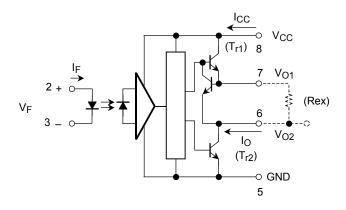
TLP557

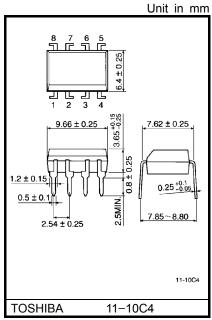
Transistor Inverter Inverter For Air Conditioner Power Transistor Base Drive

The TOSHIBA TLP557 consists of a GaAlAs light emitting diode and an integrated photodetector. This unit is 8-lead DIP package. TLP557 is suitable for base driving circuit of power transistor module up to 20A. External resistor needs to connect between pin 6 and pin 7. This is for constant current driving.

- Input threshold current: IF=5mA(max.)
- Guaranteed performance temperature range: $-30 \sim 70^{\circ}$ C
- Supply voltage: 16V(max.)
- Output current: ±0.3A(max.)
- Switching time (t_{pLH} / t_{pHL}): 5µs(max.)
- Isolation voltage: 2500V_{rms}(min.)
- UL recognized: UL1577, file No. E67349

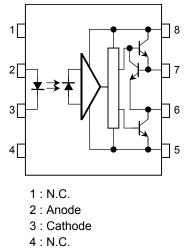
Schematic





Weight: 0.54g

Pin Configuration (top view)



- 5 : GND
- 6 : V_{O2}(Output)
- 7 : V_{O1}(Rex Terminal)
- 8 : V_{CC}

Truth Table

		Tr1	Tr2		
Input	On	On	Off		
LED	Off	Off	On		

Absolute Maximum Ratings

	Characteristic		Symbol	Rating	Unit
	Forward current		IF	25	mA
LED	Peak transient forward current	(Note 1)	IFPT	1	А
	Reverse voltage		V _R	5	V
	Junction temperature	.		125	°C
	Output current (f ≤ 5kHz, Duty ≤ 50%)		lo	+0.32 / -0.32	А
	Peak output current (P _W ≤ 10µs, f ≤ 5kHz)		I _{OP}	+2 / -0.5	А
	Output voltage		Vo	16	V
Detector			V _{CC}	16	V
Dete	O ₁ terminal to O ₂ terminal (pin 7–pin 6) voltage		V ₁₋₂	1.5	V
	O ₂ terminal to O ₁ terminal (pin 6–pin 7) voltage		V ₂₋₁	5	V
	Power dissipation (Note 2)		Po	0.5	W
	Junction temperature		(T _j)	125	°C
Total	Total package power dissipation (Note 3)		Рот	0.55	W
Operating temperature range		T _{opr}	-30~70	°C	
Stora	Storage temperature range		T _{stg}	-55~125	°C
Lead	Lead solder temperature (10 s)		T _{sol}	260	°C
Isolation voltage (AC, 1 min., R.H.≤ 60%, Ta=25°C) (Note 4)		BVS	BV _S 2500		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

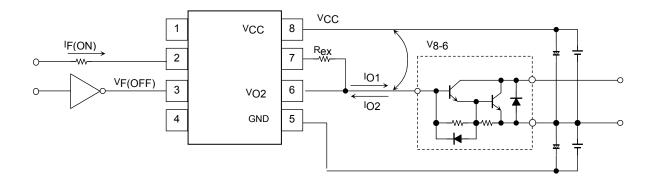
- (Note 1) Pulse width PW \leq 1µs, 300pps
- (Note 2) $\Delta P_0 / ^{\circ}C = -6.7 \text{mW} / ^{\circ}C$ (Ta $\geq 50^{\circ}C$)
- (Note 3) $\Delta P_{OT} / ^{\circ}C = -7.4 \text{mW} / ^{\circ}C \text{ (Ta } \ge 50^{\circ}C\text{)}$
- (Note 4) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

Recommended Operating Condition

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Input current on	I _F (ON)	7	8	20	mA
Input voltage off	V _F (OFF)	0	—	0.8	V
Supply voltage	V _{CC}	5	6	13	V
I _{B1} Drive current	I _{O1}	—	0.15	0.25	A
I _{B2} Drive current	I _{O2}	—	—	0.5	A
External resistance	Rex	2.7	4.3	—	Ω
V _{CC} –V _{O2} (pin 8–pin 6) ON voltage	V ₈₋₆	2.3	3 (I _{O1} = 0.15A)	2.5 (I _{O1} = 0.25A)	V
Operating temperature	Topr	-30	25	70	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

(Rex is for constant current driving)



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Electrical Characteristics (Ta = $-30 \sim 70^{\circ}$ C, unless otherwise specified)

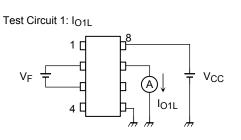
Characteristic	Symbol	Test Condition		Min.	Тур.*	Max.	Unit	Test Cir– cuit
Input forward voltage	VF	I _F = 5mA , Ta = 25°C		—	1.55	1.7	V	
Temperature coefficient of forward voltage	ΔV _F / ΔTa	I _F = 5mA	I _F = 5mA		-2.0		mV / °C	
Input reverse current	I _R	V _R = 5V, Ta = 25°C		_	_	10	μA	
Input capacitance	CT	V = 0 , f = 1MHz , Ta =	25°C	_	_	250	pF	
O1 Output leakage current	I _{O1L}	V _{CC} = 16V, V _{O1} = 0, V _F	= = 0.8V	—	0.01	200	μA	1
O ₂ Output leakage current	I _{O2L}	V _{CC} = 16V, V _{O2} = 16V, I _F = 5mA		_	0.2	200	μA	2
		V ₈₋₆ = 2.3V	V _{CC} = 6V	0.22	0.27	0.32		
O ₁ Output current	IO	Rex = 2.7Ω I _F = 5mA, Ta = 25°C	V _{CC} = 16V	0.22	0.27	0.32	A	3
O ₂ High level output voltage	V _{OH}	V_{CC} = 6V, Rex = 2.7 Ω I _F = 5mA	•	3.5	5.5		V	4
O ₂ Low level output voltage	V _{OL}	$V_{\rm F}$ = 0.8V, Rex = 2.7 Ω I _O = 0.25A, Ta = 25°C	V _{CC} = 6V	_	0.2	0.4		
			V _{CC} = 16V	_	0.2	0.4	V	_
		$V_F = 0.8V$, Rex = 2.7 Ω $I_O = 0.5A$ (*1) Ta = 25°C	V _{CC} = 6V	_	0.4	_	v	5
			V _{CC} = 16V	_	0.4	-		
	Іссн	V _{CC} = 6V, I _F = 5mA Rex = 2.7Ω, Ta = 25°C		_	3.8	10	mA	
High level supply current		V_{CC} = 6V, I _F = 5mA, Rex = 2.7 Ω		_		13		
		V_{CC} = 16V, I _F = 5mA, Rex = 2.7 Ω		_	5.2	17		
	ICCL	V _{CC} = 6V, I _F = 0mA Rex = 2.7Ω, Ta = 25°C		_	11	17	mA	
Low level supply current		V_{CC} = 6V, I _F = 0mA, Rex = 2.7 Ω		_	_	22		
		V_{CC} = 16V, I _F = 0mA, Rex = 2.7 Ω		_	13	25		
"Output L→H" threshold input current	IFLH	Rex = 2.7Ω I _O = 0.25A V _{O2} > 3V	V _{CC} = 6V	—	2.5	5	- mA	
			V _{CC} = 16V	-	-	5		
"Output H→L" threshold input current	V _{FHL}	Rex = 2.7Ω I _O = 0.25A V _{O2} < 0.4V	V _{CC} = 6V	0.8	-	_		
			V _{CC} = 16V	0.8		_	V	
Input current hysterisis	I _{HYS}	V _{CC} = 6V, Rex = 2.7Ω, Ta = 25°C		—	0.05	_	mA	
Supply voltage	V _{CC}			5	_	16	V	
Capacitance (input-output)	CS	V _S = 0, f = 1MHz, Ta = 25°C		—	1.0	2.0	pF	
Resistance (input-output)	R _S	V _S = 500V , Ta = 25℃, R.H.≤ 60%		5×10 ¹⁰	10 ¹²	_	Ω	

* All typical values are at Ta = 25°C (*1): Duration of I_O time \leq 100 μs

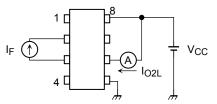
Switching Characteristics (Ta = -30~70°C unless otherwise specified)

Characteristic	Symbol	Test Condition	Min.	Тур.*	Max.	Unit	Test Cir– cuit
Propagation delay time, $L \rightarrow H$	tpLH		_	1	5	μs	
Propagation delay time, H→L	tpHL	V _{CC} = 6V, I _F = 8mA Rex = 2.7Ω	_	1	5	μs	6
Output rise time	tr	f = 5kHz, Duty = 10%	_	0.05	_	μs	0
Output fall time	t _f		_	0.05	_	μs	
Common mode transient immunity at high level output	C _{MH}	$V_{CM} = 600V, I_F = 8mA$ $V_{CC} = 6V, Rex = 270\Omega$ $R = 1k\Omega, Ta = 25^{\circ}C$	-2000	_	_	V / µs	7
Common mode transient immunity at low level output	C _{ML}	$V_{CM} = 600V, I_F = 0mA$ $V_{CC} = 6V, Rex = 270\Omega$ $R = 1k\Omega, Ta = 25^{\circ}C$	2000	_	_	V / µs	7

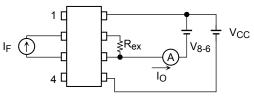
* All typical values are at Ta = 25°C.



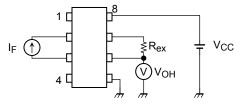
Test Circuit 2: IO2L

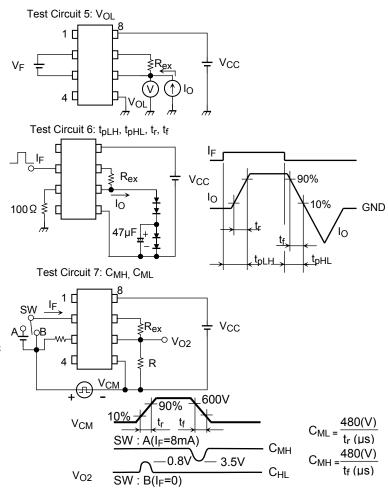


Test Circuit 3: IO



Test Circuit 4: V_{OH}





 C_{ML} (C_{MH}) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

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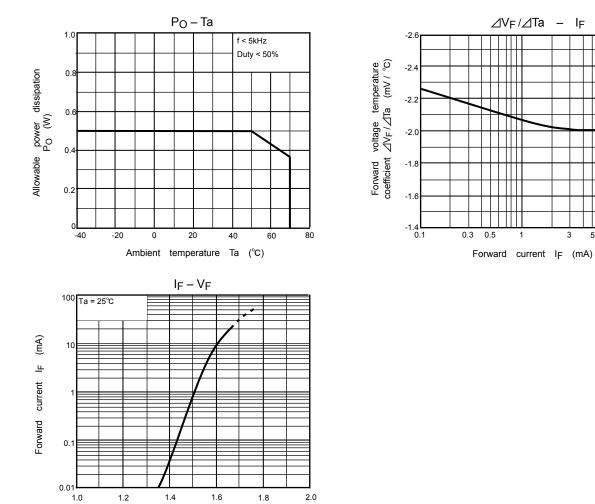
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⊿V_F/⊿Ta – I_F

1

3 5

0.5



Forward voltage V_F (V)

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20070701-EN

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